

# Plastic Infrared Emitting Diode

OP266AA, OP266AC, OP266AD  
 Obsolete (OP266AB)



## Features:

- T-1 (3 mm) package style
- Narrow irradiance pattern
- Dome lens
- Higher power output than GaAs at equivalent drive currents
- 850 nm diode

## Description:

Each device in the **OP266AA** series is a high intensity gallium aluminum arsenide infrared emitting diode (GaAlAs) that is molded in an IR transmissive clear or amber-tinted epoxy package with a dome lens. Devices feature a narrow source irradiance pattern and a variety of electrical characteristics. The small T-1 package style makes these devices ideal for space-limited applications.

These devices are mechanically and spectrally matched to other OPTEK products as follows:

*The OP266AA family conform to the OP506 and OP535 series devices.*

*Please refer to Application Bulletins 208 and 210 for additional design information and reliability (degradation) data.*

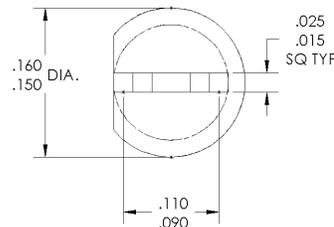
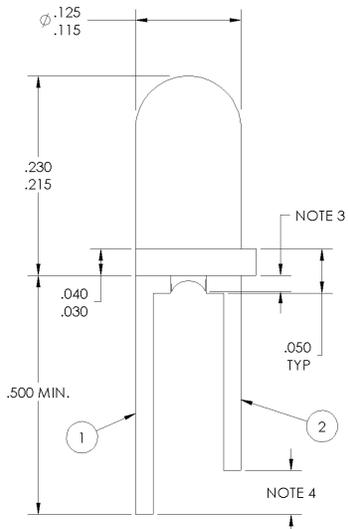
## Applications:

- Space-limited applications
- Applications requiring coupling efficiency
- Battery-operated or voltage-limited applications

Ordering Information					
Part Number	LED Peak Wavelength	Output Power (mW/cm <sup>2</sup> ) Min / Max	I <sub>F</sub> (mA) Typ / Max	Total Beam Angle	Lead Length
OP266AA	850 nm	5.5 / NA	20 / 50	18°	MIN 0.100"
OP266AB (Obsolete)		7.5 / 12.5			
OP266AC		11.5 / 16.5			
OP266AD		15.5 / NA			

### NOTES:

1. Outside discrete shell is polysulfone CLEAR.
2. This LED is built with a GaAlAs chip.
3. Max allowable epoxy miniscus is 0.030".
4. For identification purposes, Cathode lead is .065" ± .035" longer than the anode lead.
5. Dimensions are in inches.



Pin #	LED
1	Cathode
2	Anode

### CONTAINS POLYSULFONE

To avoid stress cracking, we suggest using ND Industries' **Vibra-Tite** for thread-locking. **Vibra-Tite** evaporates fast without causing structural failure in OPTEK'S molded plastics.



General Note  
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### Electrical Specifications

#### Absolute Maximum Ratings ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Storage and Operating Temperature Range	-40° C to +100° C
Reverse Voltage	2.0 V
Continuous Forward Current	50 mA
Peak Forward Current (1 $\mu\text{s}$ pulse width, 300 pps)	3.0 A
Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 seconds with soldering iron]	260° C <sup>(1)</sup>
Power Dissipation	100 mW <sup>(2)</sup>

#### Notes:

1. RMA flux is recommended. Duration can be extended to 10 second maximum when flow soldering. A maximum of 20 grams force may be applied to the leads when soldering.
2. Derate linearly at 1.33 mW/° C above 25° C.
3.  $E_{E(\text{APT})}$  is a measurement of the average apertured radiant incidence upon a sensing area 0.081" (2.06 mm) in diameter, perpendicular to and centered on the mechanical axis of the lens and 0.590" (14.99 mm) from the measurement surface.  $E_{E(\text{APT})}$  is not necessarily uniform within the measured area.

#### Electrical Characteristics ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
<b>Input Diode</b>						
$E_{E(\text{APT})}$	Apertured Radiant Incidence OP266AA OP266AC OP266AD	5.50 11.50 15.50	- - -	- 16.5 -	mW/cm <sup>2</sup>	$I_F = 20\text{ mA}$ Aperture = 0.081" diameter Distance = 0.590" from seating surface to aperture surface
$V_F$	Forward Voltage	-	-	1.80	V	$I_F = 20\text{ mA}$
$I_R$	Reverse Current	-	10	-	$\mu\text{A}$	$V_R = 10\text{ V}$
$\lambda_P$	Wavelength at Peak Emission	-	850	-	nm	$I_F = 10\text{ mA}$
$\Delta\lambda_P/\Delta T$	Spectral Shift with Temperature	-	$\pm 0.18$	-	nm/°C	$I_F = \text{Constant}$
$\theta_{HP}$	Emission Angle at Half Power Points	-	18	-	Degree	$I_F = 20\text{ mA}$
$t_r$	Output Rise Time	-	10	-	ns	$I_{F(\text{PK})} = 100\text{ mA}$ , PW = 10 $\mu\text{s}$ , D.C. = 10.0 %
$t_f$	Output Fall Time	-	10	-	ns	$I_{F(\text{PK})} = 100\text{ mA}$ , PW = 10 $\mu\text{s}$ , D.C. = 10.0 %

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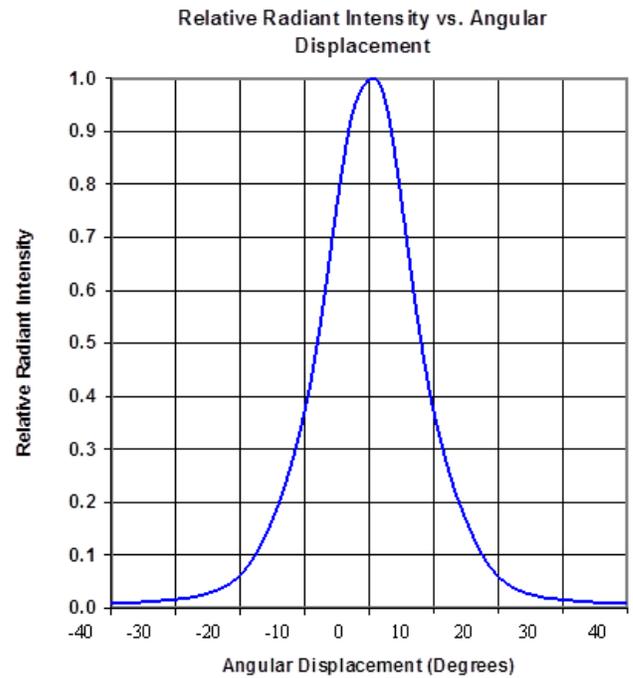
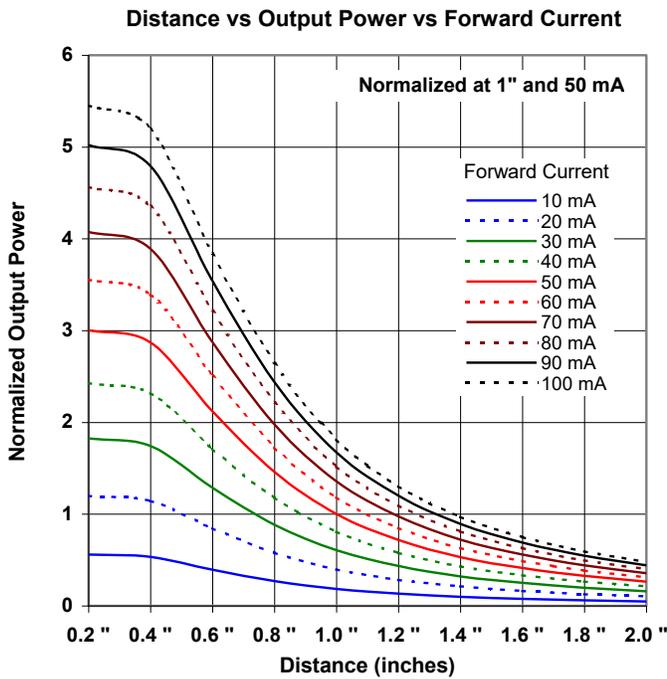
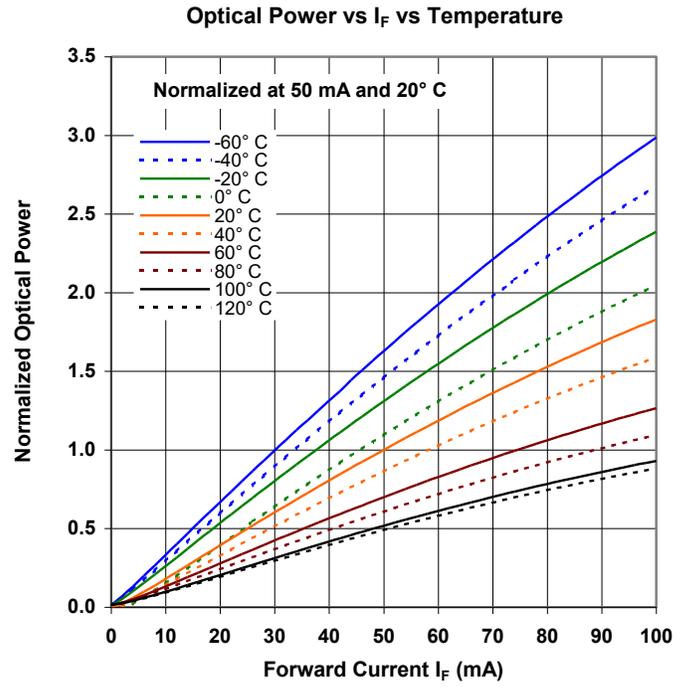
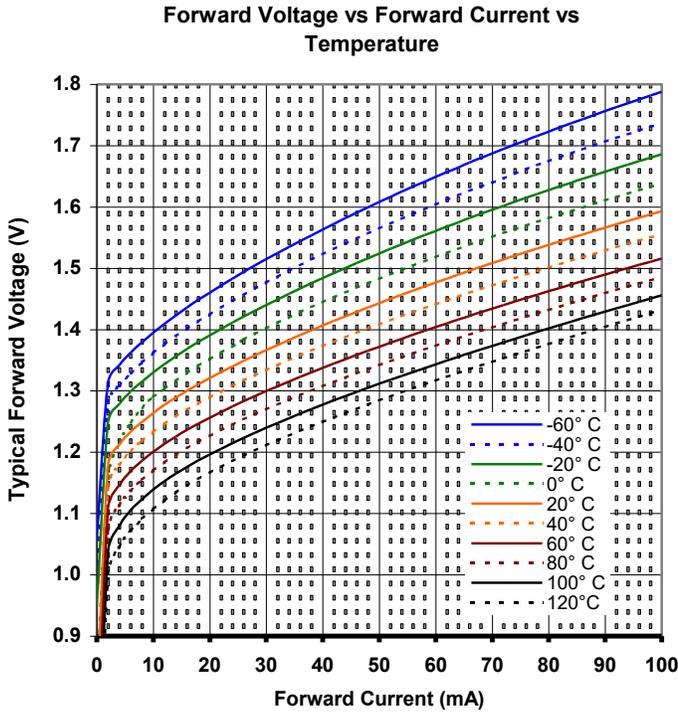
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## Performance OP266AA, AC, AD



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